

Semiconductor Physics And Devices Basic Principles

This book provides one of the most rigorous treatments of compound semiconductor device physics yet published. A complete understanding of modern devices requires a working knowledge of low-dimensional physics, the use of statistical methods, and the use of one-, two-, and three-dimensional analytical and numerical analysis techniques. With its systematic and detailed discussion of these topics, this book is ideal for both the researcher and the student. Although the emphasis of this text is on compound semiconductor devices, many of the principles discussed will also be useful to those interested in silicon devices. Each chapter ends with exercises that have been designed to reinforce concepts, to complement arguments or derivations, and to emphasize the nature of approximations by critically evaluating realistic conditions. One of the most rigorous treatments of compound semiconductor device physics yet published

Essential reading for a complete understanding of modern devices

Includes chapter-ending exercises to facilitate understanding

From physical process to practical applications - Singh makes the complexities of modern semiconductor devices clear! The semiconductor devices that are driving today's information, technologies may seem remarkably complex, but they don't have to be impossible to understand. Filled with figures, flowcharts, and solved examples, Jasprit Singh's Semiconductor Devices provides an accessible, well-balanced introduction to semiconductor physics and its application to modern devices. Beginning with the physical process behind semiconductor devices, Singh clearly explains difficult topics, including bandstructure, effective masses, holes, doping, carrier transport, and lifetimes. Following these physical fundamentals, you'll explore the operation of important semiconductor devices, such as diodes, transistors, light emitters, and detectors, along with issues relating to the optimization of device performance. Features Over 150 solved examples, integrated throughout the text, clarify difficult concepts. End-of-chapter summary tables and hundreds of figures reinforce the intricacies of modern semiconductor devices. Discussion of device optimization issues explains why you have to trade one performance against another in devices. Shows the relationship of physical parameters to SPICE parameters and its impact on circuit issues. Technology Roadmaps outline what's currently happening in the field and present a look at where device technology is headed in the future. A Bit of History sections, included in each chapter, explore the history of the concepts developed and provide a snapshot of the personalities involved and the challenges of the time.

This book is a comprehensive text on the physics of semiconductors and nanostructures for a large spectrum of students at the final undergraduate level studying physics, material science and electronics engineering. It offers introductory and advanced courses on solid state and semiconductor physics on one hand and the physics of low dimensional semiconductor structures on the other in a single text book. Key Features Presents basic concepts of quantum theory, solid state physics, semiconductors, and quantum nanostructures such as quantum well, quantum wire, quantum dot and superlattice In depth description of semiconductor heterojunctions, lattice strain and modulation doping technique Covers transport in nanostructures under an electric and magnetic field with the topics: quantized conductance, Coulomb blockade, and integer and fractional quantum Hall effect Presents the optical processes in nanostructures under a magnetic field Includes illustrative problems with hints for solutions in each chapter Physics of Semiconductors and Nanostructures will be helpful to students initiating PhD work in the field of semiconductor nanostructures and devices. It follows a unique tutorial approach meeting the requirements of students who find learning the concepts difficult and want to study from a physical perspective.

Excellent bridge between general solid-state physics textbook and research articles packed with providing detailed explanations of the electronic, vibrational, transport, and optical

properties of semiconductors "The most striking feature of the book is its modern outlook ... provides a wonderful foundation. The most wonderful feature is its efficient style of exposition ... an excellent book." Physics Today "Presents the theoretical derivations carefully and in detail and gives thorough discussions of the experimental results it presents. This makes it an excellent textbook both for learners and for more experienced researchers wishing to check facts. I have enjoyed reading it and strongly recommend it as a text for anyone working with semiconductors ... I know of no better text ... I am sure most semiconductor physicists will find this book useful and I recommend it to them." Contemporary Physics Offers much new material: an extensive appendix about the important and by now well-established, deep center known as the DX center, additional problems and the solutions to over fifty of the problems at the end of the various chapters.

Market_Desc: · Electrical Engineers Special Features: · Over 150 solved examples that clarify concepts are integrated throughout the text. · End-of-chapter summary tables and hundreds of figures are included to reinforce the intricacies of modern semiconductor devices· Coverage of device optimization issues shows the reader how in each device one has to trade one performance against another About The Book: This introductory text presents a well-balanced coverage of semiconductor physics and device operation and shows how devices are optimized for applications. The text begins with an exploration of the basic physical processes upon which all semiconductor devices are based. Next, the author focuses on the operation of the important semiconductor devices along with issues relating to the optimization of device performance.

This book presents physics-based models of bipolar power semiconductor devices and their implementation in MATLAB and Simulink. The devices are subdivided into different regions, and the operation in each region, along with the interactions at the interfaces, are analyzed using basic semiconductor physics equations that govern their behavior. The Fourier series solution is used to solve the ambipolar diffusion equation in the lightly doped drift region of the devices. In addition to the external electrical characteristics, internal physical and electrical information, such as the junction voltages and the carrier distribution in different regions of the device, can be obtained using the models. Key words: power semiconductor devices; physics-based model; Fourier series solution; drift region, carrier diffusion, transient switching behavior The 3rd edition of this successful textbook contains ample material for a comprehensive upper-level undergraduate or beginning graduate course, guiding readers to the point where they can choose a special topic and begin supervised research. The textbook provides a balance between essential aspects of solid-state and semiconductor physics, on the one hand, and the principles of various semiconductor devices and their applications in electronic and photonic devices, on the other. It highlights many practical aspects of semiconductors such as alloys, strain, heterostructures, nanostructures, that are necessary in modern semiconductor research but typically omitted in textbooks. Coverage also includes additional advanced topics, such as Bragg mirrors, resonators, polarized and magnetic semiconductors, nanowires, quantum dots, multi-junction solar cells, thin film transistors, carbon-based nanostructures and transparent conductive oxides. The text derives explicit formulas for many results to support better understanding of the topics. The Physics of Semiconductors requires little or no prior knowledge of solid-state physics and evolved from a highly regarded two-semester course. In the third edition several topics are extended and treated in more depth including surfaces, disordered materials, amorphous semiconductors, polarons, thermopower and noise. More than 1800 references guide the reader to historic and current literature including original and review papers and books.

Modern Semiconductor Devices for Integrated Circuits, First Edition introduces readers to the world of modern semiconductor devices with an emphasis on integrated circuit applications.

KEY TOPICS: Electrons and Holes in Semiconductors; Motion and Recombination of Electrons

and Holes; Device Fabrication Technology; PN and Metal–Semiconductor Junctions; MOS Capacitor; MOS Transistor; MOSFETs in ICs—Scaling, Leakage, and Other Topics; Bipolar Transistor. MARKET: Written by an experienced teacher, researcher, and expert in industry practices, this succinct and forward-looking text is appropriate for anyone interested in semiconductor devices for integrated circuits, and serves as a suitable reference text for practicing engineers.

Introduction to Semiconductor Device Physics is a popular and established text that offers a thorough introduction to the underlying physics of semiconductor devices. It begins with a review of basic solid state physics, then goes on to describe the properties of semiconductors including energy bands, the concept of effective mass, carrier concentration, and conduction in more detail. Thereafter the book is concerned with the principles of operation of specific devices, beginning with the Gunn Diode and the p-n junction. The remaining chapters cover the on specific devices, including the LED, the bipolar transistor, the field-effect transistor, and the semiconductor laser. The book concludes with a chapter providing a brief introduction to quantum theory. Not overtly mathematical, Introduction to Semiconductor Device Physics introduces only those physical concepts required for an understanding of the semiconductor devices being considered. The author's intuitive style, coupled with an extensive set of worked problems, make this the ideal introductory text for those concerned with understanding electrical and electronic engineering, applied physics, and related subjects.

This textbook provides a theoretical background for contemporary trends in solid-state theory and semiconductor device physics. It discusses advanced methods of quantum mechanics and field theory and is therefore primarily intended for graduate students in theoretical and experimental physics who have already studied electrodynamics, statistical physics, and quantum mechanics. It also relates solid-state physics fundamentals to semiconductor device applications and includes auxiliary results from mathematics and quantum mechanics, making the book useful also for graduate students in electrical engineering and material science. Key Features: Explores concepts common in textbooks on semiconductors, in addition to topics not included in similar books currently available on the market, such as the topology of Hilbert space in crystals Contains the latest research and developments in the field Written in an accessible yet rigorous manner

Provides a basis for understanding the characteristics, operation, and limitations of semiconductor devices. This title deals with the electrical properties and characteristics of semiconductor materials and devices. It intends to bring together quantum mechanics, the quantum theory of solids, and semiconductor material physics.

This book is an introduction to the principles of semiconductor physics, linking its scientific aspects with practical applications. It is addressed to both readers who wish to learn semiconductor physics and those seeking to understand semiconductor devices. It is particularly well suited for those who want to do

both. Intended as a teaching vehicle, the book is written in an expository manner aimed at conveying a deep and coherent understanding of the field. It provides clear and complete derivations of the basic concepts of modern semiconductor physics. The mathematical arguments and physical interpretations are well balanced: they are presented in a measure designed to ensure the integrity of the delivery of the subject matter in a fully comprehensible form. Experimental procedures and measured data are included as well. The reader is generally not expected to have background in quantum mechanics and solid state physics beyond the most elementary level. Nonetheless, the presentation of this book is planned to bring the student to the point of research/design capability as a scientist or engineer. Moreover, it is sufficiently well endowed with detailed knowledge of the field, including recent developments bearing on submicron semiconductor structures, that the book also constitutes a valuable reference resource. In Chapter 1, basic features of the atomic structures, chemical nature and the macroscopic properties of semiconductors are discussed. The band structure of ideal semiconductor crystals is treated in Chapter 2, together with the underlying one-electron picture and other fundamental concepts. Chapter 2 also provides the requisite background of the tight binding method and the k.p-method, which are later used extensively. The electron states of shallow and deep centers, clean semiconductor surfaces, quantum wells and superlattices, as well as the effects of external electric and magnetic fields, are treated in Chapter 3. The one- or multi-band effective mass theory is used wherever this method is applicable. A summary of group theory for application in semiconductor physics is given in an Appendix. Chapter 4 deals with the statistical distribution of charge carriers over the band and localized states in thermodynamic equilibrium. Non-equilibrium processes in semiconductors are treated in Chapter 5. The physics of semiconductor junctions (pn-, hetero-, metal-, and insulator-) is developed in Chapter 6 under conditions of thermodynamic equilibrium, and in Chapter 7 under non-equilibrium conditions. On this basis, the most important electronic and opto-electronic semiconductor devices are treated, among them uni- and bipolar transistors, photodetectors, solar cells, and injection lasers. A summary of group theory for applications in semiconductors is given in an Appendix.

This book demonstrates the role and abilities of fluctuation in semiconductor physics, and shows what kinds of physical information are involved in the noise characteristics of semiconductor materials and devices, how this information may be decoded and which advantages are inherent to the noise methods. The text provides a comprehensive account of current results, addressing problems which have not previously been covered in Western literature, including the excess noise of tunnel-recombination currents and photocurrents in diodes, fluctuation phenomena in a real photoconductor with different recombination centers, and methods of noise spectroscopy of levels in a wide range of materials and devices.

Fundamentals of Semiconductor Devices is a comprehensively written text which

deals with both qualitative and quantitative analysis of semiconductor theory & devices. This book is perfect for the first course on Semiconductor Physics and Devices at the UG level.

A detailed description of the basic physics of semiconductors. All the important equations describing the properties of these materials are derived without the help of other textbooks. The reader is assumed to have only a basic command of mathematics and some elementary semiconductor physics. The text covers a wide range of important semiconductor phenomena, from the simple to the advanced.

This book provides an overview of compound semiconductor materials and their technology. After presenting a theoretical background, it describes the relevant material preparation technologies for bulk and thin-layer epitaxial growth. It then briefly discusses the electrical, optical, and structural properties of semiconductors, complemented by a description of the most popular characterization tools, before more complex hetero- and low-dimensional structures are discussed. A special chapter is devoted to GaN and related materials, owing to their huge importance in modern optoelectronic and electronic devices, on the one hand, and their particular properties compared to other compound semiconductors, on the other. In the last part of the book, the physics and functionality of optoelectronic and electronic device structures (LEDs, laser diodes, solar cells, field-effect and heterojunction bipolar transistors) are discussed on the basis of the specific properties of compound semiconductors presented in the preceding chapters of the book. Compound semiconductors form the back-bone of all opto-electronic and electronic devices besides the classical Si electronics. Currently the most important field is solid state lighting with highly efficient LEDs emitting visible light. Also laser diodes of all wavelength ranges between mid-infrared and near ultraviolet have been the enabler for a huge number of unprecedented applications like CDs and DVDs for entertainment and data storage, not to speak about the internet, which would be impossible without optical data communications with infrared laser diodes as key elements. This book provides a concise overview over this class of materials, including the most important technological aspects for their fabrication and characterisation, also covering the most relevant devices based on compound semiconductors. It presents therefore an excellent introduction into this subject not only for students, but also for engineers and scientist who intend to put their focus on this field of science.

Semiconductor Physics and Devices provides an introduction to the physics of semiconductor materials and devices. The text is supported by a large number of examples and exercises to test the understanding of topics.

Optoelectronics has become an important part of our lives. Wherever light is used to transmit information, tiny semiconductor devices are needed to transfer electrical current into optical signals and vice versa. Examples include light emitting diodes in radios and other appliances, photodetectors in elevator doors and digital cameras, and laser diodes that transmit phone calls through glass fibers. Such optoelectronic devices take advantage of sophisticated

interactions between electrons and light. Nanometer scale semiconductor structures are often at the heart of modern optoelectronic devices. Their shrinking size and increasing complexity make computer simulation an important tool to design better devices that meet ever rising performance requirements. The current need to apply advanced design software in optoelectronics follows the trend observed in the 1980's with simulation software for silicon devices. Today, software for technology computer-aided design (TCAD) and electronic design automation (EDA) represents a fundamental part of the silicon industry. In optoelectronics, advanced commercial device software has emerged recently and it is expected to play an increasingly important role in the near future. This book will enable students, device engineers, and researchers to more effectively use advanced design software in optoelectronics. Provides fundamental knowledge in semiconductor physics and in electromagnetics, while helping to understand and use advanced device simulation software Demonstrates the combination of measurements and simulations in order to obtain realistic results and provides data on all required material parameters Gives deep insight into the physics of state-of-the-art devices and helps to design and analyze of modern optoelectronic devices

The purpose of this book is to provide the reader with a self-contained treatment of fundamental solid state and semiconductor device physics. The material presented in the text is based upon the lecture notes of a one-year graduate course sequence taught by this author for many years in the Department of Electrical Engineering of the University of Florida. It is intended as an introductory textbook for graduate students in electrical engineering. However, many students from other disciplines and backgrounds such as chemical engineering, materials science, and physics have also taken this course sequence, and will be interested in the material presented herein. This book may also serve as a general reference for device engineers in the semiconductor industry. The present volume covers a wide variety of topics on basic solid state physics and physical principles of various semiconductor devices. The main subjects covered include crystal structures, lattice dynamics, semiconductor statistics, energy band theory, excess carrier phenomena and recombination mechanisms, carrier transport and scattering mechanisms, optical properties, photoelectric effects, metal-semiconductor devices, the p-n junction diode, bipolar junction transistor, MOS devices, photonic devices, quantum effect devices, and high speed III-V semiconductor devices. The text presents a unified and balanced treatment of the physics of semiconductor materials and devices. It is intended to provide physicists and materials scientists with more device backgrounds, and device engineers with a broader knowledge of fundamental solid state physics.

This book covers the physics of semiconductors on an introductory level, assuming that the reader already has some knowledge of condensed matter physics. Crystal structure, band structure, carrier transport, phonons, scattering processes and optical properties are presented for typical semiconductors such as silicon, but III-V and II-VI compounds are also included. In view of the increasing importance of wide-gap semiconductors, the electronic and optical properties of these materials are dealt with too.

Electrical Engineering Advanced Theory of Semiconductor Devices Semiconductor devices are ubiquitous in today's world and are found increasingly in cars, kitchens and electronic door locks, attesting to their presence in our daily lives. This comprehensive book provides the fundamentals of semiconductor device theory from basic quantum physics to computer-aided design. Advanced Theory of Semiconductor Devices will improve your understanding of computer simulation of devices through a thorough discussion of basic equations, their validity, and numerical solutions as they are contained in current simulation tools. You will gain state-of-the-art knowledge of devices used in both III-V compounds and silicon technology. Specially featured are novel approaches and explanations of electronic transport, particularly in p-n junction diodes. Close attention is also given to innovative treatments of quantum-well laser

diodes and hot electron effects in silicon technology. This in-depth book is written for engineers, graduate students, and research scientists in solid-state electronics who want to gain a better understanding of the principles underlying semiconductor devices.

Special Features

- *Computer-based exercises and homework problems -- unique to this text and comprising 25% of the total number of problems -- encourage students to address realistic and challenging problems, experiment with what if scenarios, and easily obtain graphical outputs. Problems are designed to progressively enhance MATLAB-use proficiency, so students need not be familiar with MATLAB at the start of your course. Program scripts that are answers to exercises in the text are available at no charge in electronic form (see Teaching Resources below).
- *Supplement and Review Mini-Chapters after each of the text's three parts contain an extensive review list of terms, test-like problem sets with answers, and detailed suggestions on supplemental reading to reinforce students' learning and help them prepare for exams.
- *Read-Only Chapters, strategically placed to provide a change of pace during the course, provide informative, yet enjoyable reading for students.
- *Measurement Details and Results samples offer students a realistic perspective on the seldom-perfect nature of device characteristics, contrary to the way they are often represented in introductory texts.

Content Highlig

"The textbook combines a thorough theoretical treatment of the basic physics of semiconductors with applications to practical devices by putting special emphasis on the physical principles upon which these devices operate. - "Graduate students and lecturers in semiconductor physics, condensed matter physics, electromagnetic theory, and quantum mechanics will find this a useful textbook and reference work."--Jacket.

This textbook describes the basic physics of semiconductors, including the hierarchy of transport models, and connects the theory with the functioning of actual semiconductor devices. Details are worked out carefully and derived from the basic physical concepts, while keeping the internal coherence of the analysis and explaining the different levels of approximation. Coverage includes the main steps used in the fabrication process of integrated circuits: diffusion, thermal oxidation, epitaxy, and ion implantation. Examples are based on silicon due to its industrial importance. Several chapters are included that provide the reader with the quantum-mechanical concepts necessary for understanding the transport properties of crystals. The behavior of crystals incorporating a position-dependent impurity distribution is described, and the different hierarchical transport models for semiconductor devices are derived (from the Boltzmann transport equation to the hydrodynamic and drift-diffusion models). The transport models are then applied to a detailed description of the main semiconductor-device architectures (bipolar, MOS, CMOS), including a number of solid-state sensors. The final chapters are devoted to the measuring methods for semiconductor-device parameters, and to a brief illustration of the scaling rules and numerical methods applied to the design of semiconductor devices.

The Third Edition of the standard textbook and reference in the field of semiconductor devices. This classic book has set the standard for advanced study and reference in the semiconductor device field. Now completely updated and reorganized to reflect the tremendous advances in device concepts and performance, this Third Edition remains the most detailed and exhaustive single source of information on the most important semiconductor devices. It gives readers immediate access to detailed descriptions of the underlying physics and performance characteristics of all major bipolar, field-effect, microwave, photonic, and sensor devices. Designed for graduate textbook adoptions and reference needs, this new edition includes: A complete update of the latest developments New devices such as three-dimensional MOSFETs, MODFETs, resonant-tunneling diodes, semiconductor sensors, quantum-cascade lasers, single-electron transistors, real-space transfer devices, and more Materials completely reorganized Problem sets at the end of each chapter All figures reproduced at the highest

quality Physics of Semiconductor Devices, Third Edition offers engineers, research scientists, faculty, and students a practical basis for understanding the most important devices in use today and for evaluating future device performance and limitations. A Solutions Manual is available from the editorial department.

The new edition of this textbook presents a detailed description of basic semiconductor physics. The text covers a wide range of important phenomena in semiconductors, from the simple to the advanced. Four different methods of energy band calculations in the full band region are explained: local empirical pseudopotential, non-local pseudopotential, KP perturbation and tight-binding methods. The effective mass approximation and electron motion in a periodic potential, Boltzmann transport equation and deformation potentials used for analysis of transport properties are discussed. Further, the book examines experiments and theoretical analyses of cyclotron resonance in detail. Optical and transport properties, magneto-transport, two-dimensional electron gas transport (HEMT and MOSFET) and quantum transport are reviewed, while optical transition, electron-phonon interaction and electron mobility are also addressed. Energy and electronic structure of a quantum dot (artificial atom) are explained with the help of Slater determinants. The physics of semiconductor lasers is also described, including Einstein coefficients, stimulated emission, spontaneous emission, laser gain, double heterostructures, blue lasers, optical confinement, laser modes, and strained quantum well lasers, offering insights into the physics of various kinds of semiconductor lasers. In this third edition, energy band calculations in full band zone with spin-orbit interaction are presented, showing all the matrix elements and equipping the reader to prepare computer programs of energy band calculations. The Luttinger Hamiltonian is discussed and used to analyze the valence band structure. Numerical calculations of scattering rate, relaxation time, and mobility are presented for typical semiconductors, which are very helpful for understanding of transport. Energy band structures and effective masses of nitrides such as GaN, InN, AlN and their ternary alloys are discussed because they are very important materials for the blue light emission, and high power devices with and high frequency. Learning and teaching with this textbook is supported by problems and solutions in the end of the chapters. The book is written for bachelor and upper undergraduate students of physics and engineering.

Neamen's Semiconductor Physics and Devices, Third Edition. deals with the electrical properties and characteristics of semiconductor materials and devices. The goal of this book is to bring together quantum mechanics, the quantum theory of solids, semiconductor material physics, and semiconductor device physics in a clear and understandable way.

Physics of Semiconductor Devices covers both basic classic topics such as energy band theory and the gradual-channel model of the MOSFET as well as advanced concepts and devices such as MOSFET short-channel effects, low-dimensional devices and single-electron transistors. Concepts are introduced to the reader in a simple way, often using comparisons to everyday-life experiences such as simple fluid mechanics. They are then explained in depth and mathematical developments are fully described. Physics of Semiconductor Devices contains a list of problems that can be used as homework assignments or can be solved in class to exemplify the theory. Many of these problems make use of Matlab and are aimed at illustrating theoretical concepts in a graphical manner.

Quantum Mechanics: Concepts and Applications provides a clear, balanced and modern introduction to the subject. Written with the student's background and ability in mind the book takes an innovative approach to quantum mechanics by combining the essential elements of the theory with the practical applications: it is therefore both a textbook and a problem solving book in one self-contained volume. Carefully structured, the book starts with the experimental basis of quantum mechanics and then discusses its mathematical tools. Subsequent chapters cover the formal foundations of the subject, the exact solutions of the Schrödinger equation for one and three dimensional potentials, time-independent and time-dependent approximation

methods, and finally, the theory of scattering. The text is richly illustrated throughout with many worked examples and numerous problems with step-by-step solutions designed to help the reader master the machinery of quantum mechanics. The new edition has been completely updated and a solutions manual is available on request. Suitable for senior undergraduate courses and graduate courses.

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of *Physics of Semiconductor Devices* remains the standard reference work on the fundamental physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulator-semiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, real-world examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOS-controlled thyristors *Physics of Semiconductor Devices, Fourth Edition* is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.

The first edition of "Semiconductor Physics" was published in 1973 by Springer-Verlag Wien-New York as a paperback in the Springer Study Edition. In 1977, a Russian translation by Professor Yu. K. Pozhela and coworkers at Vilnius/USSR was published by Izdatelstvo "MIR", Moscow. Since then new ideas have been developed in the field of semiconductors such as electron hole droplets, dangling bond saturation in amorphous silicon by hydrogen, or the determination of the fine structure constant from surface quantization in inversion layers. New techniques such as molecular beam epitaxy which has made the realization of the Esaki superlattice possible, deep level transient spectroscopy, and refined a. c. Hall techniques have evolved. Now that the Viennese edition is about to go out of print, Springer-Verlag, Berlin-Heidelberg-New York is giving me the opportunity to include these new subjects in a monograph to appear in the Solid-State Sciences series. Again it has been the intention to cover the field of semiconductor physics comprehensively, although some chapters such as diffusion of hot carriers and their galvanomagnetic phenomena, as well as superconducting degenerate semiconductors and the appendices, had to go for commercial reasons. The emphasis is more on physics than on device aspects.

Semiconductor Device Physics and Design teaches readers how to approach device design from the point of view of someone who wants to improve devices and can see the opportunity and challenges. It begins with coverage of basic physics concepts, including the physics

behind polar heterostructures and strained heterostructures. The book then details the important devices ranging from p-n diodes to bipolar and field effect devices. By relating device design to device performance and then relating device needs to system use the student can see how device design works in the real world.

The advent of the microelectronics technology has made ever-increasing numbers of small devices on a same chip. The rapid emergence of ultra-large-scaled-integrated (ULSI) technology has moved device dimension into the sub-quarter-micron regime and put more than 10 million transistors on a single chip. While traditional closed-form analytical models furnish useful intuition into how semiconductor devices behave, they no longer provide consistently accurate results for all modes of operation of these very small devices. The reason is that, in such devices, various physical mechanisms affect the device performance in a complex manner, and the conventional assumptions (i. e. , one-dimensional treatment, low-level injection, quasi-static approximation, etc.) employed in developing analytical models become questionable. Thus, the use of numerical device simulation becomes important in device modeling. Researchers and engineers will rely even more on device simulation for device design and analysis in the future. This book provides comprehensive coverage of device simulation and analysis for various modern semiconductor devices. It will serve as a reference for researchers, engineers, and students who require in-depth, up-to-date information and understanding of semiconductor device physics and characteristics. The materials of the book are limited to conventional and mainstream semiconductor devices; photonic devices such as light emitting and laser diodes are not included, nor does the book cover device modeling, device fabrication, and circuit applications.

The awaited revision of *Semiconductor Devices: Physics and Technology* offers more than 50% new or revised material that reflects a multitude of important discoveries and advances in device physics and integrated circuit processing. Offering a basic introduction to physical principles of modern semiconductor devices and their advanced fabrication technology, the third edition presents students with theoretical and practical aspects of every step in device characterizations and fabrication, with an emphasis on integrated circuits. Divided into three parts, this text covers the basic properties of semiconductor materials, emphasizing silicon and gallium arsenide; the physics and characteristics of semiconductor devices bipolar, unipolar special microwave and photonic devices; and the latest processing technologies, from crystal growth to lithographic pattern transfer.

Semiconductors have made an enormous impact on 20th century science and technology. This is because components made from semiconductors have very favorable properties such as low energy consumption, compactness, and high reliability, and so they now dominate electronics and radio engineering. Semiconductors are indispensable for space exploration and where the requirements of small size, low weight and low energy consumption are especially stringent. The book uses quantum-mechanical concepts and band theory to present the theory of semiconductors in a comprehensible form. It also describes how basic semiconductor devices (e.g. diodes, transistors, and lasers) operate. The book was written for senior high-school students interested in physics.

This manual contains the PLOT software, user's guide and program description to accompany Michael Shur's 'Physics of semiconductor devices' - rear cover.

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